GJ32C

PNP EPITAXIAL PLANAR TRANSISTOR

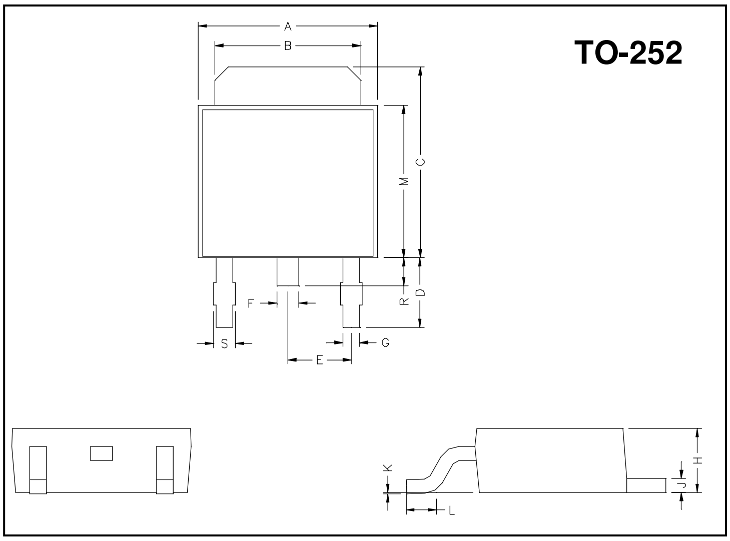
Description

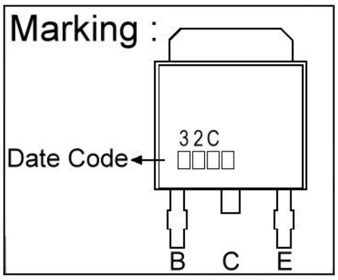
The GJ32C is designed for use in general purpose amplifier and switching applications.

Features

*Complementary to GJ31C

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.40	3.00	K	0	0.15
E	2.30 REF.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

Absolute Maximum Ratings (Ta = 25℃, unless otherwise specified)

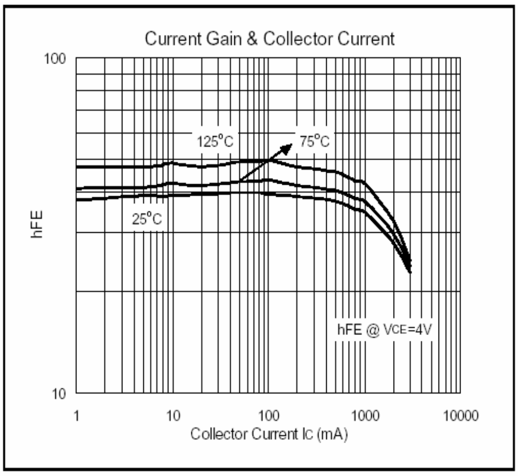
Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{CEO}	-5	V
Collector Current (DC)	I_C	-3	A
Collector Current (Pulse)	I_C	-5	A
Junction Temperature	Tj	+150	℃
Storage Temperature	T_{STG}	-55 ~ +150	℃
Total Power Dissipation	P_D	2	W
	P_D(T_C=25℃)	15	W

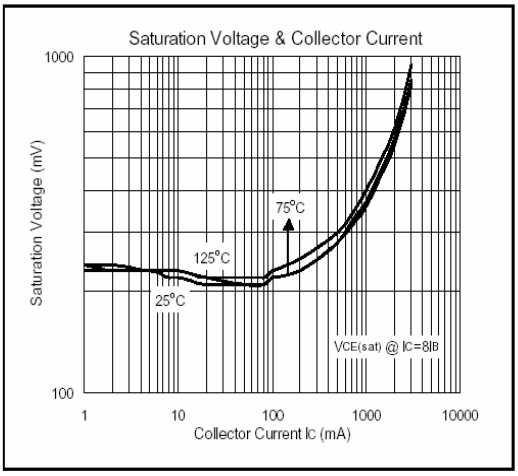
Electrical Characteristics (Rating at Ta=25℃)

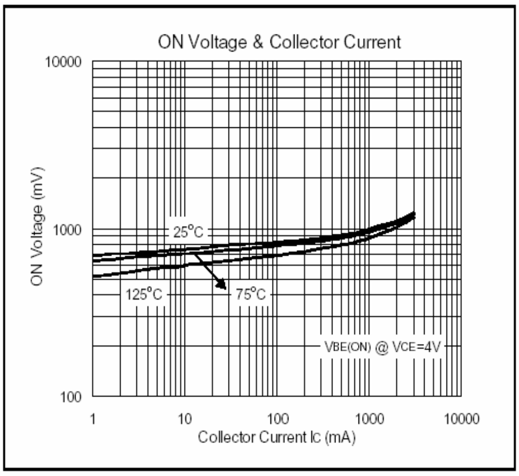
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-100	-	-	V	I_C=-1mA, I_E=0
BV_{CEO}	-100	-	-	V	I_C=-30mA, I_B=0
BV_{EBO}	-5	-	-	V	I_E=-100uA, I_C=0
I_{CES}	-	-	-20	uA	V_{CE}=-100V, V_{EB}=0V
I_{CEO}	-	-	-50	uA	V_{CE}=-60V, I_B=0
I_{EBO}	-	-	-1	mA	V_{EB}=-5V, I_C=0
*$V_{CE(sat)}$	-	-	-1.2	V	I_C =-3A, I_B=-375mA
*$V_{BE(on)}$	-	-	-1.8	V	V_{CE}=-4V, I_C=-3A
*h_{FE1}	25	-	-		V_{CE}=-4V, I_C=-1A
*h_{FE2}	10	-	50		V_{CE}=-4V, I_C=-3A
fT	3	-	-	MHz	V_{CE}=-10V, I_C=-500mA, f=1MHz

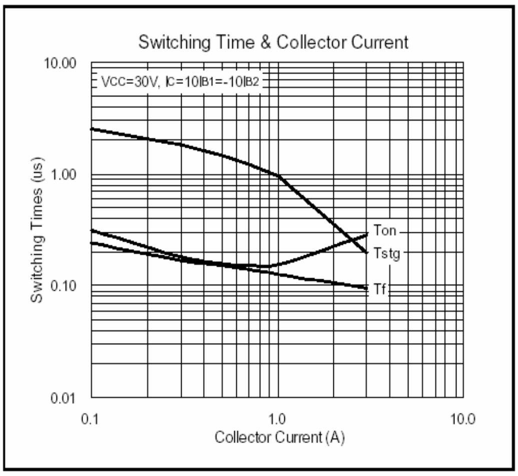
* Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%

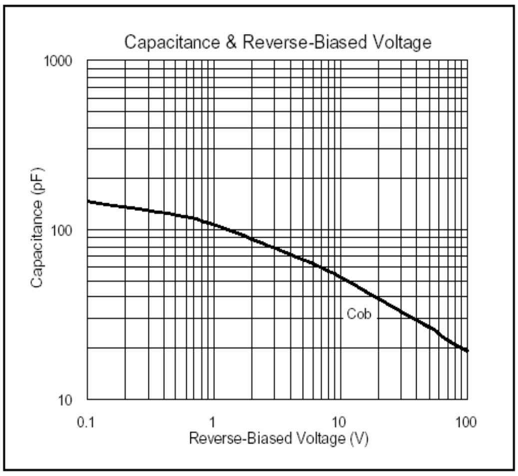
Characteristics Curve

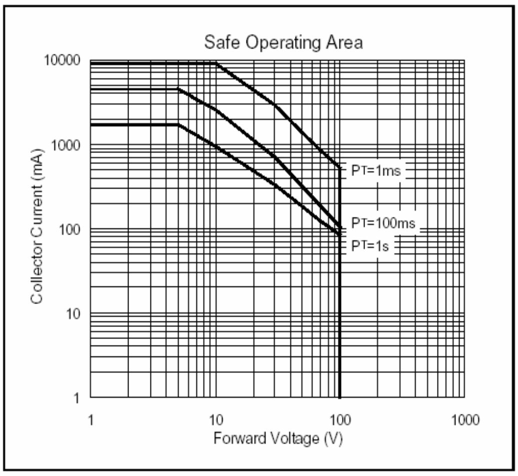












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